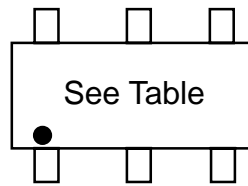
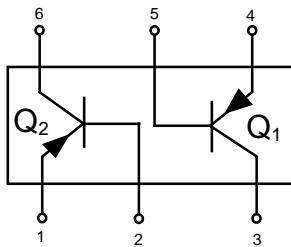


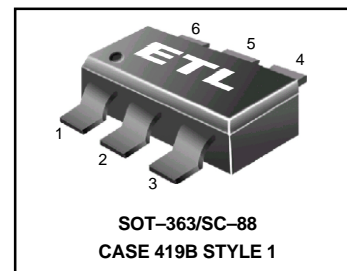
Dual General Purpose Transistors

PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.



BC856BDW1T1
BC857BDW1T1
BC857CDW1T1
BC858BDW1T1
BC858CDW1T1



MAXIMUM RATINGS

Rating	Symbol	BC856	BC857	BC858	Unit
Collector-Emitter Voltage	V_{CE0}	-65	-45	-30	V
Collector-Base Voltage	V_{CBO}	-80	-50	-30	V
Emitter-Base Voltage	V_{EBO}	-5.0	-5.0	-5.0	V
Collector Current -Continuous	I_C	-100	-100	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation	P_D	380	mW
Per Device		250	mW
FR-5 Board, (1) $T_A = 25^\circ\text{C}$			
Derate above 25°C		3.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

ORDERING INFORMATION

Device	Package	Shipping
BC856BDW1T1	SOT-363	3000 Units/Reel
BC857BDW1T1	SOT-363	3000 Units/Reel
BC857CDW1T1	SOT-363	3000 Units/Reel
BC858BDW1T1	SOT-363	3000 Units/Reel
BC858CDW1T1	SOT-363	3000 Units/Reel

BC856BDW1T1, BC857BDW1T1, BC857CDW1T1, BC858BDW1T1, BC858CDW1T1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$)	$V_{(BR)CEO}$				V
BC856 Series		-65	—	—	
BC857 Series		-45	—	—	
BC858 Series		-30	—	—	
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$)	$V_{(BR)CES}$				V
BC856 Series		-80	—	—	
BC857 Series		-50	—	—	
BC858 Series		-30	—	—	
Collector–Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$)	$V_{(BR)CBO}$				V
BC856 Series		-80	—	—	
BC857 Series		-50	—	—	
BC858 Series		-30	—	—	
Emitter–Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$)	$V_{(BR)EBO}$				V
BC856 Series		-5.0	—	—	
BC857 Series		-5.0	—	—	
BC858 Series		-5.0	—	—	
Collector Cutoff Current ($V_{CB} = -30\text{ V}$)	I_{CBO}	—	—	-15	nA
($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$)		—	—	-4.0	μA

ON CHARACTERISTICS

DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$)	h_{FE}				—
BC856B, BC857B, BC858B		—	150	—	
BC857C, BC858C		—	270	—	
($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$)		220	290	475	
BC856B, BC857B, BC858B		420	520	800	
Collector–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$)	$V_{CE(sat)}$	—	—	-0.3	V
($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)		—	—	-0.65	
Base–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$)	$V_{BE(sat)}$	—	-0.7	—	V
($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)		—	-0.9	—	
Base–Emitter Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$)	$V_{BE(on)}$	-0.6	—	-0.75	V
($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$)		—	—	-0.82	

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	—	—	MHz
Output Capacitance ($V_{CB} = -10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	—	—	4.5	pF
Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	—	—	10	dB

**BC856BDW1T1, BC857BDW1T1, BC857CDW1T1
BC858BDW1T1, BC858CDW1T1**

TYPICAL PNP CHARACTERISTICS — BC856

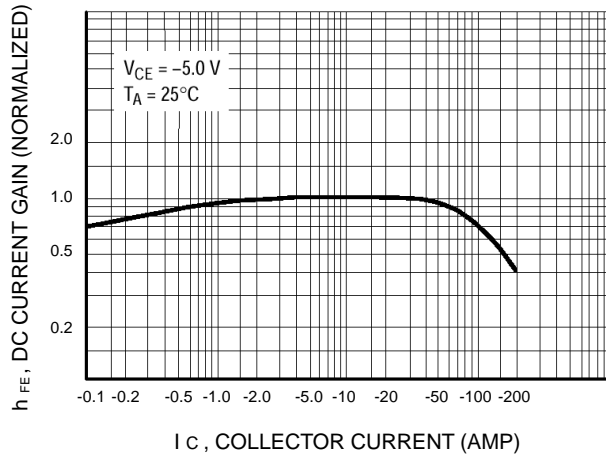


Figure 1. DC Current Gain

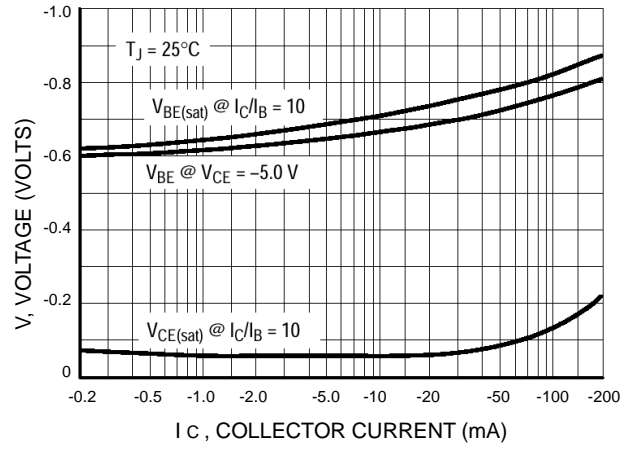


Figure 2. "On" Voltage

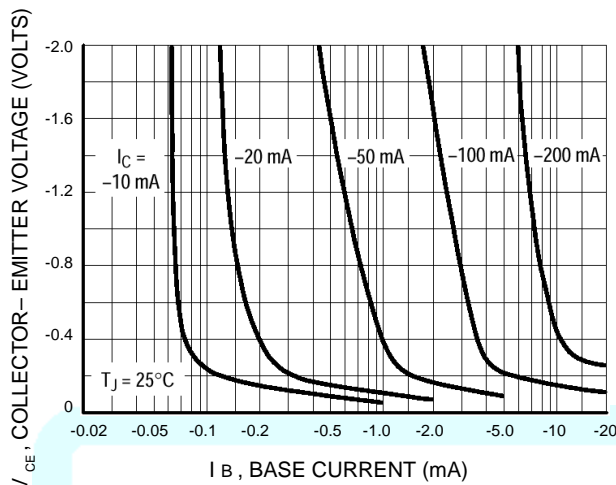


Figure 3. Collector Saturation Region

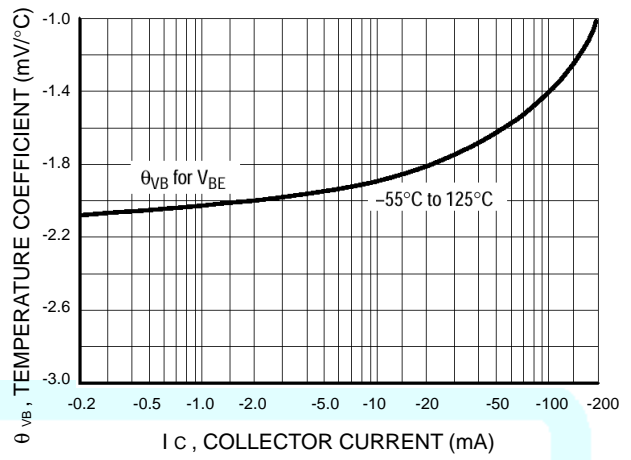


Figure 4. Base-Emitter Temperature Coefficient

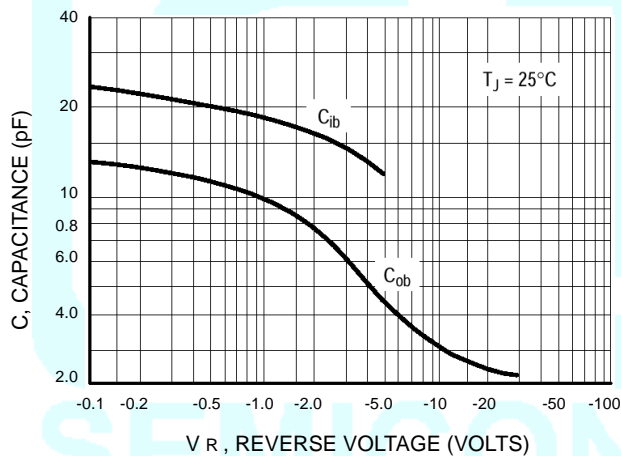


Figure 5. Capacitance

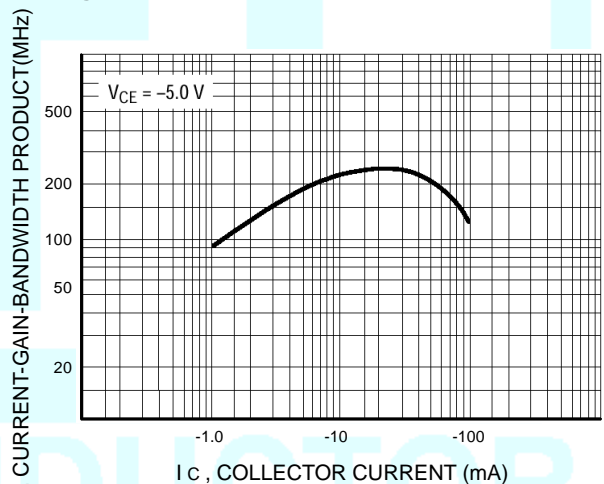


Figure 6. Current-Gain - Bandwidth Product

**BC856BDW1T1, BC857BDW1T1, BC857CDW1T1
BC858BDW1T1, BC858CDW1T1**

TYPICAL PNP CHARACTERISTICS — BC857/BC858

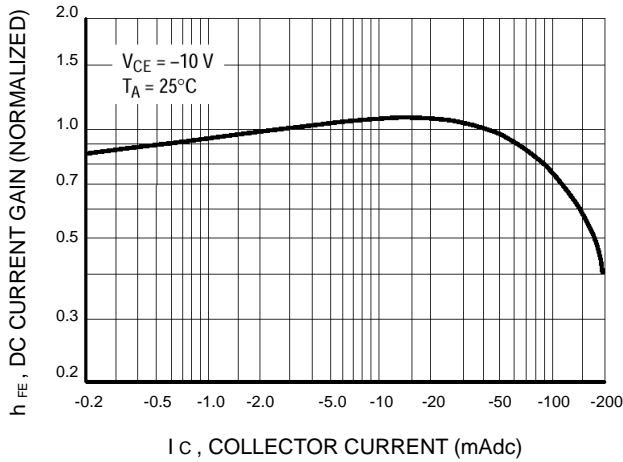


Figure 7. Normalized DC Current Gain

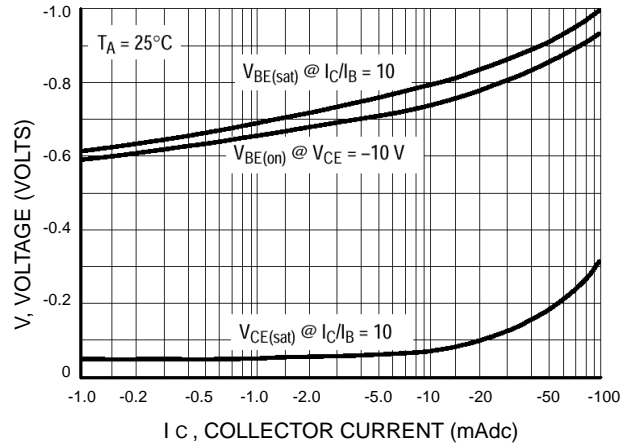


Figure 8. "Saturation" and "On" Voltages

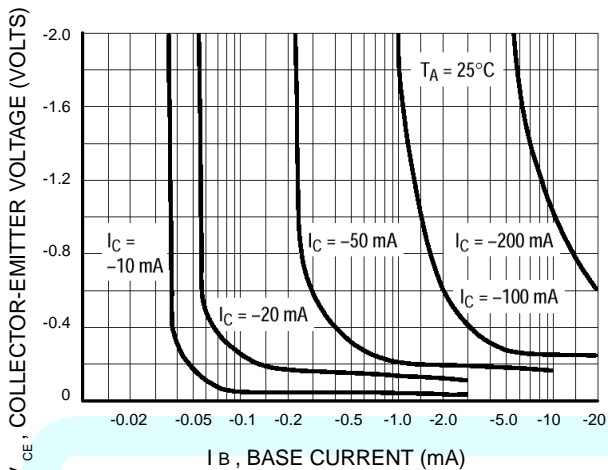


Figure 9. Collector Saturation Region

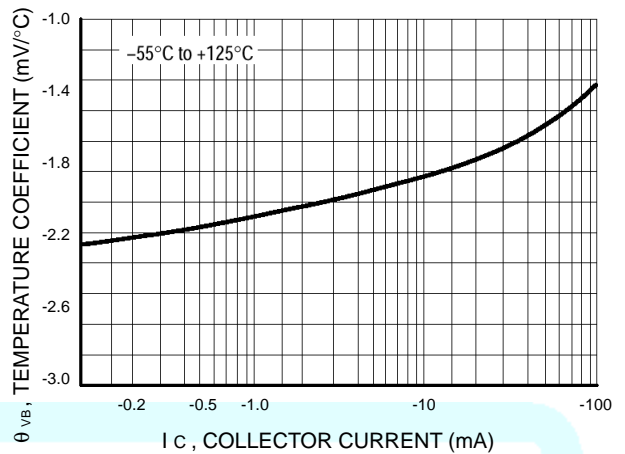


Figure 10. Base-Emitter Temperature Coefficient

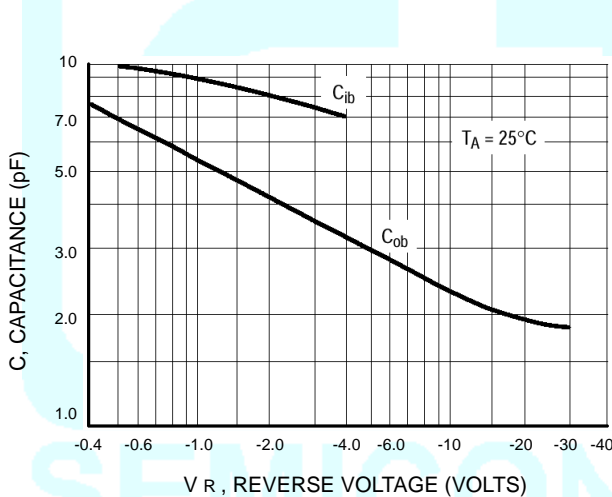


Figure 11. Capacitance

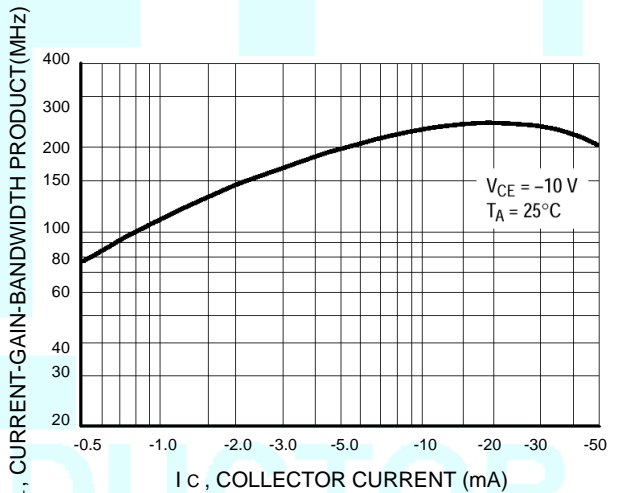


Figure 12. Current-Gain-Bandwidth Product

BC846BDW1T1, BC847BDW1T1, BC847CDW1T1, BC848BDW1T1, BC848CDW1T1

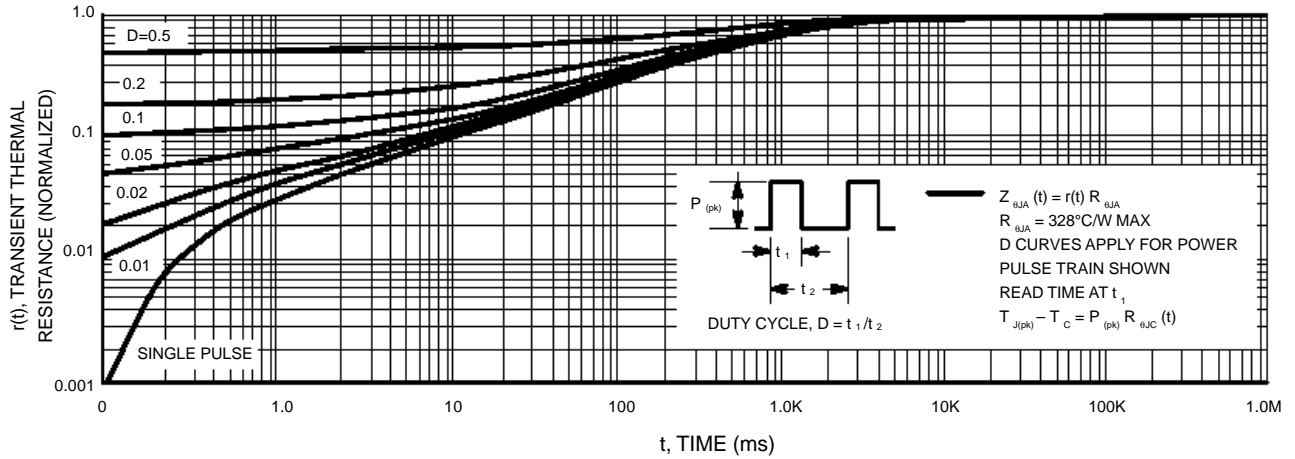


Figure 13. Thermal Response

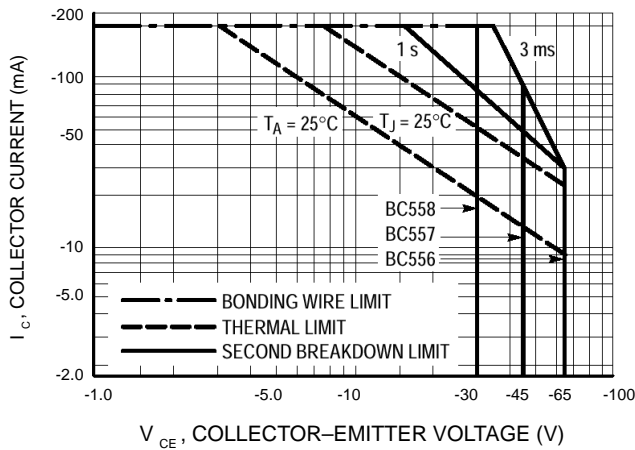


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

